

MOSFETs Silicon N-Channel MOS

SSM6N67NU

1. Applications

- · Power Management Switches
- · DC-DC Converters

2. Features

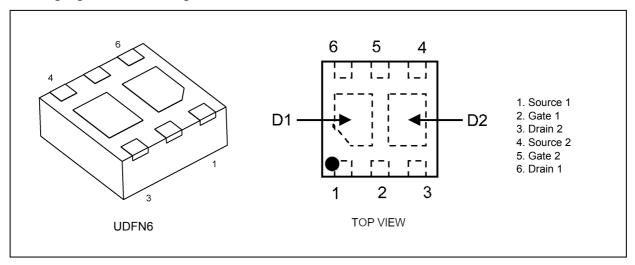
- (1) AEC-Q101 qualified (Note 1)
- (2) 1.8-V gate drive voltage.
- (3) Low drain-source on-resistance
 - : $R_{DS(ON)}$ = 39.1 m Ω (max) (@ V_{GS} = 4.5 V)

 $R_{\mathrm{DS(ON)}} = 53 \ \mathrm{m}\Omega \ (\mathrm{max}) \ (@V_{\mathrm{GS}} = 2.5 \ \mathrm{V})$

 $R_{\mathrm{DS(ON)}} = 82~\mathrm{m}\Omega~(\mathrm{max})~(@V_{\mathrm{GS}} = 1.8~\mathrm{V})$

Note 1: For detail information, please contact our sales.

3. Packaging and Pin Assignment





4. Absolute Maximum Ratings (Note) (Unless otherwise specified, T_a = 25 °C) (Q1,Q2 Common)

	Characteristics			Symbol	Rating	Unit
Drain-source voltage				V_{DSS}	30	V
Gate-source voltage				V_{GSS}	12/-8	
Drain current (DC)			(Note 1)	Ι _D	4	Α
Drain current (pulsed)			(Note 1), (Note 2)	I_{DP}	10	
Power dissipation			(Note 3)	P_{D}	1	W
Power dissipation	(t ≤	10 s)	(Note 3)	P _D	2	W
Channel temperature				T _{ch}	150	°C
Storage temperature				T _{stg}	-55 to 150	

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

- Note 1: Ensure that the channel temperature does not exceed 150 °C.
- Note 2: Pulse width (PW) \leq 10 ms, duty \leq 1 %
- Note 3: Device mounted on an FR-4 board.(total dissipation) (25.4 mm \times 25.4 mm \times 1.6 mm ,Cu pad: 645 mm²)

Note: The MOSFETs in this device are sensitive to electrostatic discharge. When handling this device, the worktables, operators, soldering irons and other objects should be protected against anti-static discharge.

Note: The channel-to-ambient thermal resistance, R_{th(ch-a)}, and the drain power dissipation, P_D, vary according to the board material, board area, board thickness and pad area. When using this device, be sure to take heat dissipation fully into account.

5. Thermal Characteristics

Characteristics		Symbol	Max	Unit
Channel-to-ambient thermal resistance	(Note 1)	R _{th(ch-a)}	125	°C/W

Note 1: Device mounted on an 25.4 mm × 25.4 mm × 1.6 mm FR4 glass epoxy board (Cu pad: 645 mm²)



6. Electrical Characteristics

6.1. Static Characteristics (Unless otherwise specified, T_a = 25 °C)(Q1,Q2 Common)

Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current		I _{GSS}	V _{DD} = 0 V, V _{GS} = 10/-8 V	_	_	±10	μА
Drain cut-off current		I _{DSS}	V _{DS} = 24 V, V _{GS} = 0 V	_	_	1	
Drain-source breakdown voltage		V _{(BR)DSS}	I _D = 1 mA, V _{GS} = 0 V	30	_	_	٧
Drain-source breakdown voltage	(Note 1)	V _{(BR)DSX}	I _D = 1 mA, V _{GS} = -8 V	18	_	_	
Gate threshold voltage	(Note 2)	V _{th}	V _{DS} = 3 V, I _D = 1 mA	0.40	_	1.00	
Drain-source on-resistance	(Note 3)	R _{DS(ON)}	I _D = 2.0 A, V _{GS} = 4.5 V	_	30	39.1	mΩ
			I _D = 1.0 A, V _{GS} = 2.5 V	_	37	53	
			I _D = 0.5 A, V _{GS} = 1.8 V	_	46	82	
Forward transfer admittance	(Note 3)	Y _{fs}	V _{DS} = 3 V, I _D = 2.0 A	6.0	12.0	_	S

- Note 1: If a reverse bias is applied between gate and source, this device enters $V_{(BR)DSX}$ mode. Note that the drain-source breakdown voltage is lowered in this mode.
- Note 2: Let V_{th} be the voltage applied between gate and source that causes the drain current (I_D) to below (1 mA for this device). Then, for normal switching operation, $V_{GS(ON)}$ must be higher than V_{th} , and $V_{GS(OFF)}$ must be lower than V_{th} . This relationship can be expressed as: $V_{GS(OFF)} < V_{th} < V_{GS(ON)}$.

 Take this into consideration when using the device.

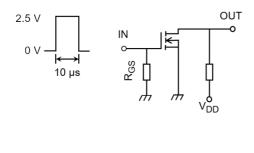
Note 3: Pulse measurement.

6.2. Dynamic Characteristics (Unless otherwise specified, T_a = 25 °C) (Q1,Q2 Common)

Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance		C _{iss}	$V_{DS} = 15 \text{ V}$, $V_{GS} = 0 \text{ V}$,	_	310	_	pF
Reverse transfer capacitance		C _{rss}	f = 1 MHz	_	20	_	
Output capacitance		C _{oss}		_	52	_	
Switching time (turn-on time)	(Note 1)	t _{on}	V _{DD} = 15 V, I _D = 1.0 A,	_	26		ns
Switching time (turn-off time)	(Note 1)	t _{off}	V_{GS} = 0 to 2.5 V, R_{GS} = 4.7 Ω	_	17	_	

Note 1: See chapter 6.3

6.3. Switching Time Test Circuit



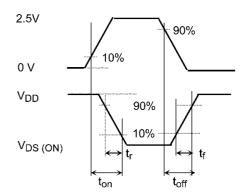


Fig. 6.3.1 Switching Time Test Circuit

Fig. 6.3.2 Input Waveform/Output Waveform



6.4. Gate Charge Characteristics (Unless otherwise specified, T_a = 25 °C) (Q1,Q2 Common)

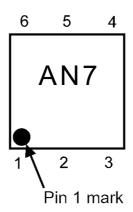
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus gate-drain)	Qg	V_{DD} = 15 V, I_{D} = 4.0 A,	_	3.2	_	nC
Gate-source charge 1	Q _{gs1}	V _{GS} = 4.5 V	_	0.5	_	
Gate-drain charge	Q _{gd}			0.7		

6.5. Source-Drain Characteristics (Unless otherwise specified, T_a = 25 °C) (Q1,Q2 Common)

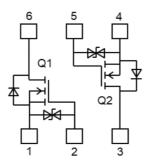
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Diode forward voltage (No	te 1) V _{DSF}	I _{DR} = 4.0 A, V _{GS} = 0 V	_	0.8	1.2	V

Note 1: Pulse measurement.

7. Marking



8. Internal Equivalent Circuit





100

80

60

40

20

Drain–source on-resistance RDs(ON) $(m\Omega)$

9. Characteristics Curves (Q1,Q2 Common) (Note)

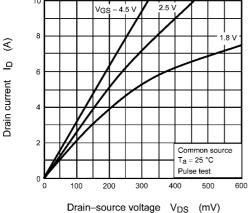
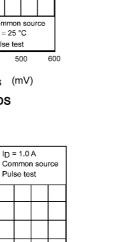


Fig. 9.1 $I_D - V_{DS}$



25 °C

100 °C

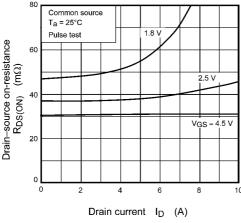


Fig. 9.5 R_{DS(ON)} - I_D

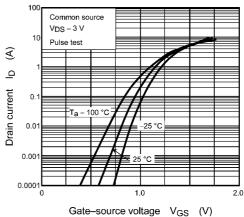


Fig. 9.2 I_D - V_{GS}

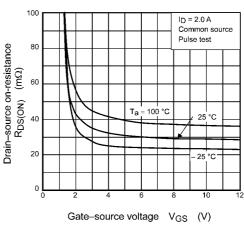


Fig. 9.4 R_{DS(ON)} - V_{GS}

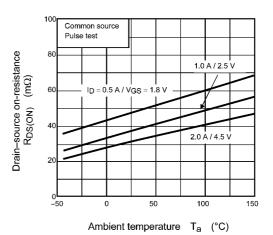
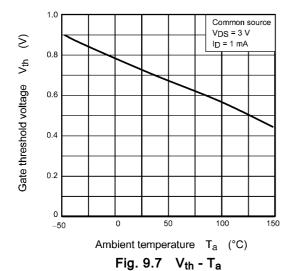


Fig. 9.6 R_{DS(ON)} - T_a





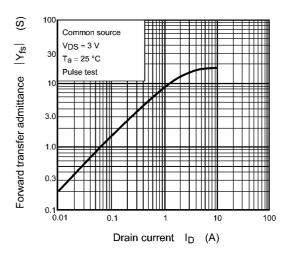
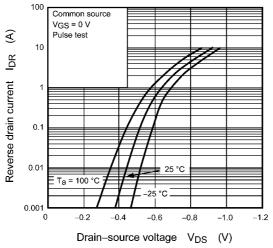
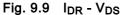


Fig. 9.8 |Y_{fs}| - I_D





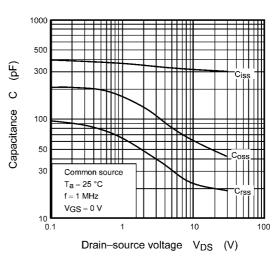


Fig. 9.10 C - V_{DS}

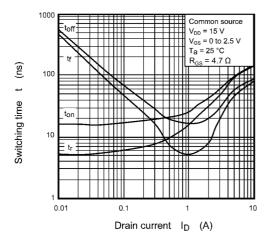


Fig. 9.11 t - I_D

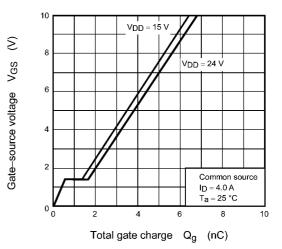
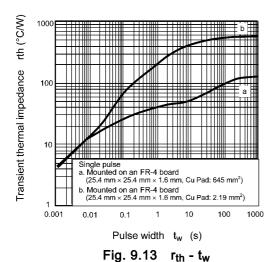


Fig. 9.12 Dynamic Input Characteristics





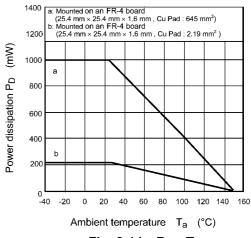


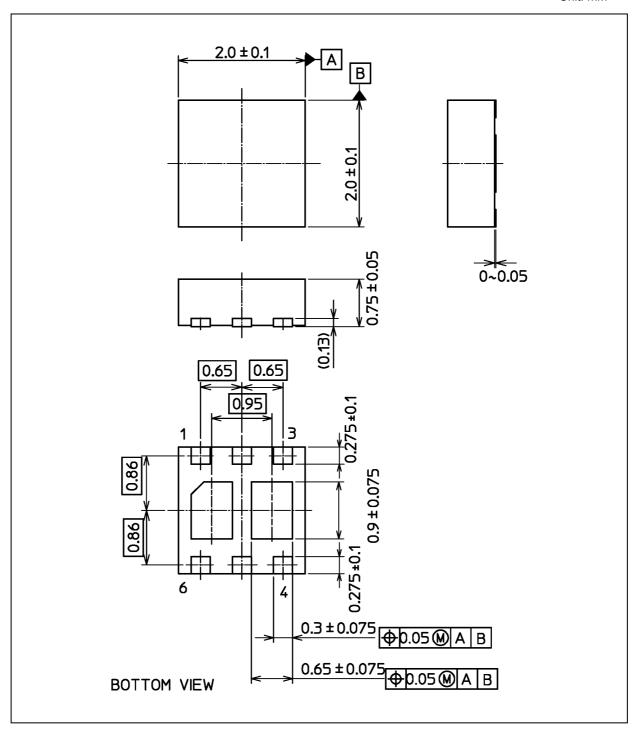
Fig. 9.14 PD - Ta

Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



Package Dimensions

Unit: mm



Weight: 8.5 mg (typ.)

	Package Name(s)
Nickname: UDFN6	



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